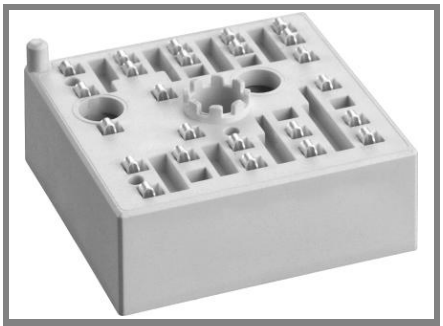
SKiiP 11NAB066V1



MiniSKiiP® 1

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter

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Target Data

Features

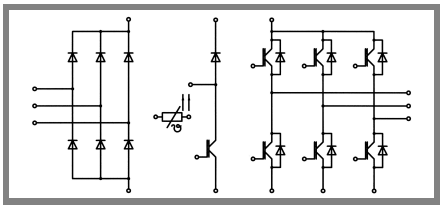
- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

- Inverter up to 3,5 kVA
- Typical motor power 1,5 kW

Remarks

- Case temperature limited to T_C = 125 °C max.



NAB

Absolute Maximum Ratings	T_s = 25 °C, unless otherwise specified		
Symbol	**Conditions**	**Values**	**Units**
IGBT - Inverter, Chopper			
V_{CES}		600	V
I_C	T_s = 25 (70) °C		A
I_{CRM}	T_s = 25 (70) °C, $t_p \leq$ 1 ms		A
V_{GES}		± 20	V
T_j		- 40 ... + 175	°C
Diode - Inverter, Chopper			
I_F	T_s = 25 (70) °C		A
I_{FRM}	T_s = 25 (70) °C, $t_p \leq$ 1 ms		A
T_j		- 40 ... + 175	°C
Diode - Rectifier			
V_{RRM}		800	V
I_F	T_s = 70 °C	35	A
I_{FSM}	t_p = 10 ms, sin 180 °, T_j = 25 °C	220	A
i^2t	t_p = 10 ms, sin 180 °, T_j = 25 °C	240	A²s
T_j		- 40 ... + 150	°C
I_{tRMS}	per power terminal (20 A / spring)	20	A
T_{stg}	$T_{op} \leq T_{stg}$	- 40 ... + 125	°C
V_{isol}	AC, 1 min.	2500	V

Characteristics	T_s = 25 °C, unless otherwise specified				
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT - Inverter, Chopper					
V_{CEsat}	I_C = 6 A, T_j = 25 (125) °C		1,45 (1,65)	1,9 (2,05)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}$, I_C = 0,5 mA		5,8		V
$V_{CE(TO)}$	T_j = 25 (125) °C		0,9 (0,85)	1 (0,9)	V
r_T	T_j = 25 (125) °C		92 (133)	150 (192)	mΩ
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		368		nF
C_{oes}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		28		nF
C_{res}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		11		nF
$R_{th(j-s)}$	per IGBT		1,9		K/W
$t_{d(on)}$	under following conditions		-		ns
t_r	V_{CC} = 300 V, V_{GE} = ± 15 V		-		ns
$t_{d(off)}$	I_C = 6 A, T_j = 125 °C		-		ns
t_f	$R_{Gon} = R_{Goff}$ = - Ω		-		ns
E_{on}	inductive load		0,15		mJ
E_{off}			0,27		mJ
Diode - Inverter, Chopper					
$V_F = V_{EC}$	I_F = 6 A, T_j = 25 (125) °C		1,4	1,6	V
$V_{(TO)}$	T_j = 25 (125) °C		0,95	1	V
r_T	T_j = 25 (125) °C		75	100	mΩ
$R_{th(j-s)}$	per diode		2,5		K/W
I_{RRM}	under following conditions		-		A
Q_{rr}	I_F = 6 A, V_R = 300 V		-		µC
E_{rr}	V_{GE} = 0 V, T_j = 125 °C				mJ
	di_F/dt = - A/µs				
Diode - Rectifier					
V_F	I_F = 15 A, T_j = 25 °C		1,1		V
$V_{(TO)}$	T_j = 150 °C		0,8		V
r_T	T_j = 150 °C		20		mΩ
$R_{th(j-s)}$	per diode		1,5		K/W
Temperature Sensor					
R_{ts}	3 %, T_r = 25 (100) °C		1000(1670)		Ω
Mechanical Data					
w			35		g
M_s	Mounting torque	2		2,5	Nm

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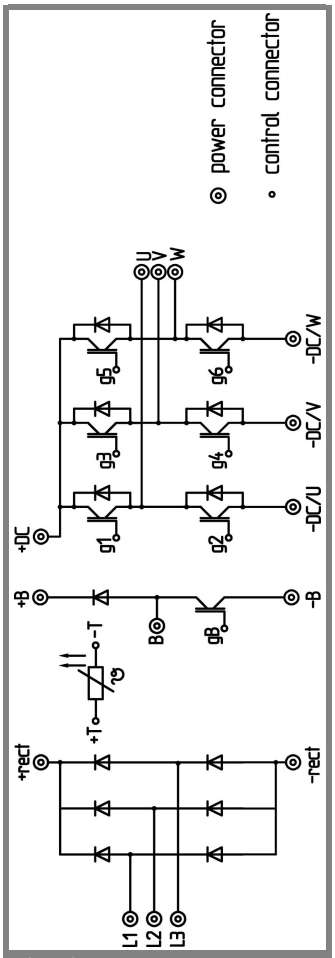
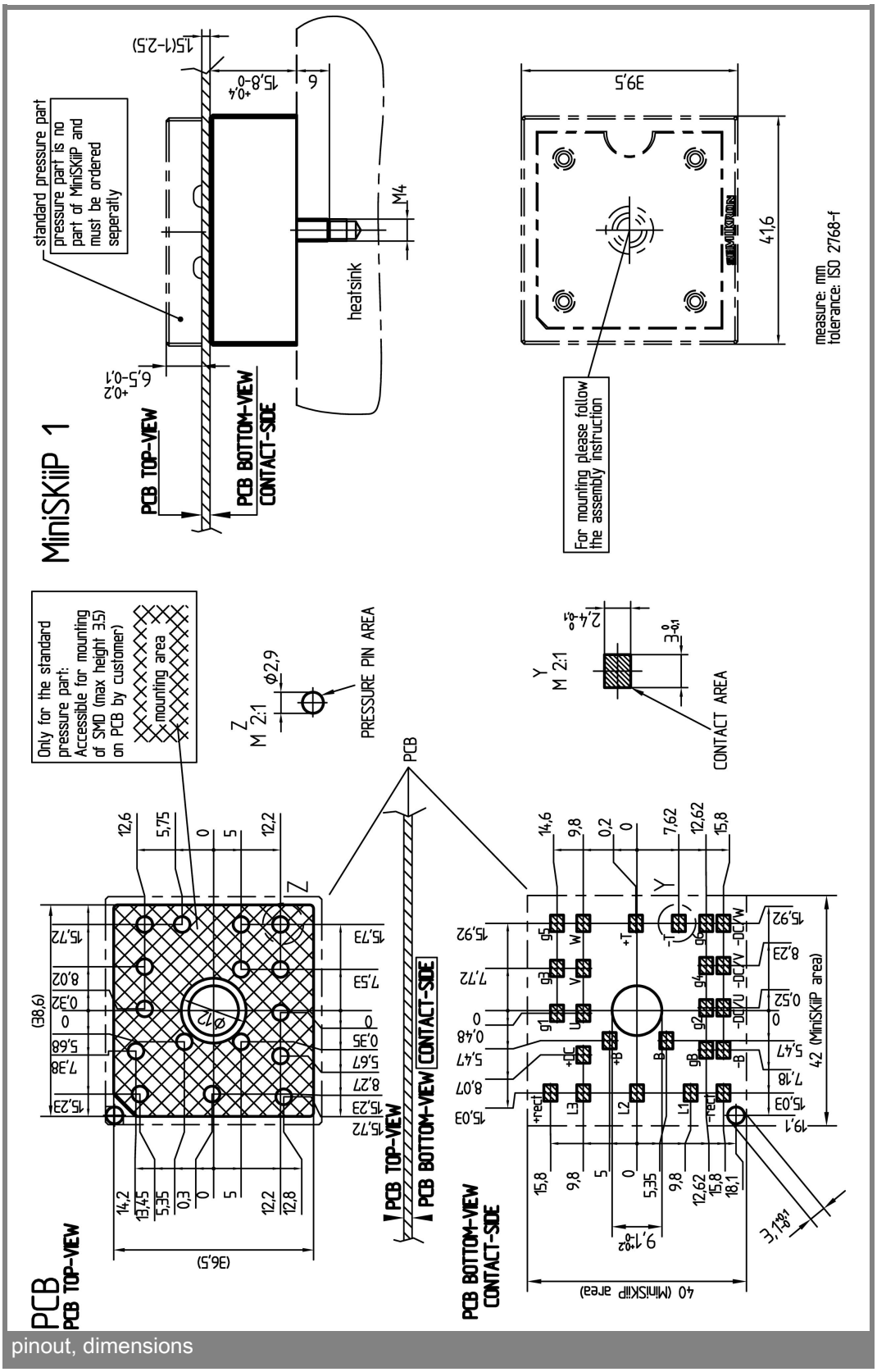


circuit



pinout, dimensions

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

